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Vishay Siliconix

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET

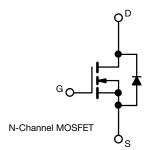


PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0058				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0090				
I <sub>D</sub> (A)	88				
Configuration	Single				
Package	PowerPAK SO-8L				

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ABSOLUTE MAXIMUM RATINGS (	T <sub>C</sub> = 25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	40	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current	T <sub>C</sub> = 25 °C	1	88	
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	51	
Continuous source current (diode conduction)		I <sub>S</sub>	90	Α
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	201	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	18	
Single pulse avalanche energy	L=0.11III	E <sub>AS</sub>	16.2	mJ
Maximum navvay discination 3	T <sub>C</sub> = 25 °C	D	75	W
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	25	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) <sup>c</sup>			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	$R_{thJA}$	42	°C/W
Junction-to-case (drain)		$R_{thJC}$	1.4	G/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							L
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	40	-	-	.,
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$		1.7	2.2	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0043	0.0058	
Due in account on state westerness 2		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0115	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.014	Ω
		V <sub>GS</sub> = 4.5 V		-	0.068	0.0090	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	52	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	1270	1780	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	380	630	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	45	65	
Total gate charge <sup>c</sup>	Qg			-	23	35	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 10 \text{ A}$	-	4	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	5	-	
Gate resistance	Rg		f = 1 MHz	1.7	3.5	5.3	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = 20 \text{ V}, \text{ R}_L = 1.0 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		5	9	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A},$			24	36	
Fall time <sup>c</sup>	t <sub>f</sub>				5	9	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	360	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	10 A, V <sub>GS</sub> = 0 V	-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>			-	21	42	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	8	16	nC
Reverse recovery fall time	t <sub>a</sub>	IF = 6	A, dl/dt = 100 A/μs	-	10	-	
Reverse recovery rise time	t <sub>b</sub>	7		-	11	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	0.7	-	Α

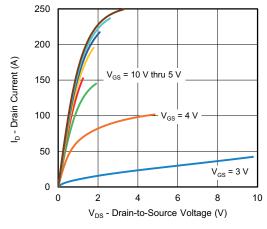
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

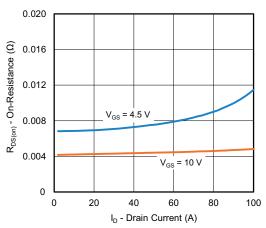
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



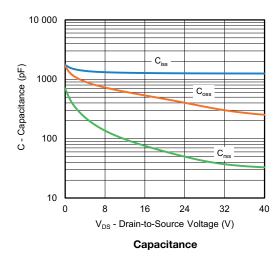
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

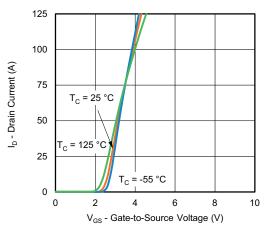


#### **Output Characteristics**

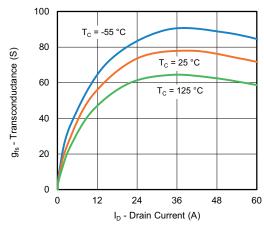


On-Resistance vs. Drain Current

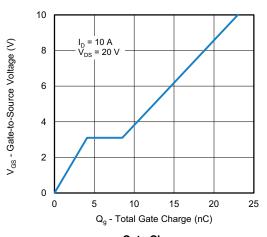




**Transfer Characteristics** 

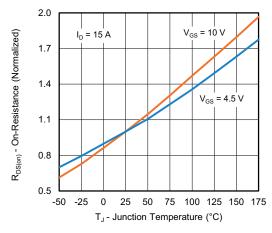


Transconductance

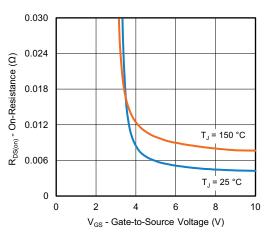




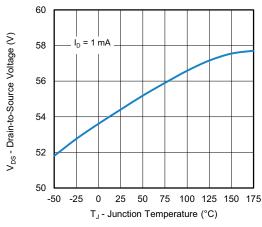
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

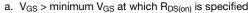


On-Resistance vs. Gate-to Source Voltage

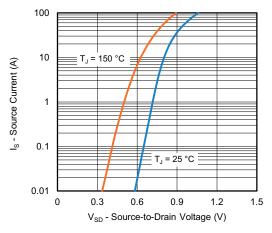


**Drain Source Breakdown vs. Junction Temperature** 

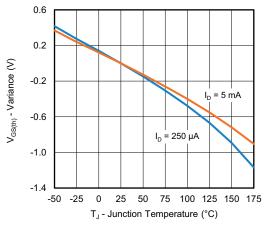
Note



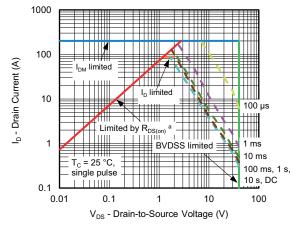
S20-0725-Rev. B, 28-Sep-2020



**Source Drain Diode Forward Voltage** 



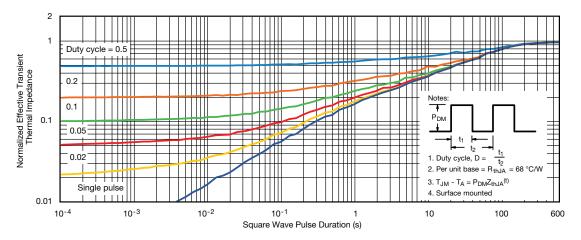
Threshold Voltage



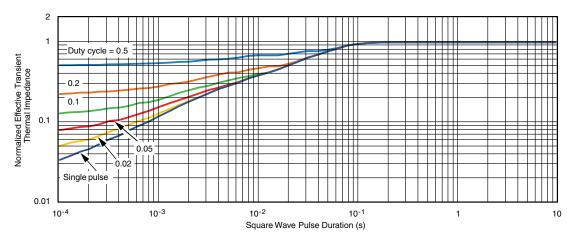
Safe Operating Area



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?77553">www.vishay.com/ppg?77553</a>.



# PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS			INCHES			
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.00	1.05	1.10	0.039	0.041	0.043		
A1	0.00		0.127	0.000		0.005		
b	0.33	0.41	0.49	0.013	0.016	0.019		
b1	0.43	0.51	0.59	0.017	0.020	0.023		
b2	4.00	4.10	4.20	0.157	0.161	0.165		
С	0.15	0.20	0.25	0.006	0.008	0.010		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D5	0.51	0.61	0.71	0.020	0.024	0.028		
D6	2.64	2.74	2.84	0.104	0.108	0.112		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
E3	3.48	3.58	3.68	0.137	0.141	0.145		
E4	2.72	2.82	2.92	0.107	0.111	0.115		
E5	0.71	0.81	0.91	0.028	0.032	0.036		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
W1	0.31	0.41	0.51	0.012	0.016	0.020		
W4	0.31	0.36	0.41	0.012	0.014	0.016		
z1	0.37	0.47	0.57	0.015	0.019	0.022		
z2	0.99	1.09	1.19	0.039	0.043	0.047		
θ	0°		5°	0°		5°		

### Note

• Millimeter will govern

Revison: 18-Sep-2023 1 Document Number: 76666



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)

Revision: 24-Aug-2021 1 Document Number: 78020



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